

NTE30047 Infrared Emitting Diode – 5mm

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Power Dissipation, P_D	100mW
Forward Current (Note 1), I_{FM}	1000mA
Reverse Voltage ($I_R = 10\mu\text{A}$), V_R	9V
Operating Temperature Range, T_{opr}	-40° to +85°C
Storage Temperature Range, T_{stg}	-40° to +100°C
Lead Temperature (During Soldering, .157" (4mm) from case bottom, 5sec max), T_L	+260°C

Note 1. Duty = 0.01ms, 1kHz

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Viewing Angle	$201/2$	$I_F = 50\text{mA}$	–	40	–	degree
Forward Voltage	V_F	$I_F = 50\text{mA}$	–	1.3	1.5	V
Reverse Current	I_R	$V_R = 5\text{V}$	–	–	10	μA
Radiant Intensity	E_e	$I_F = 50\text{mA}$	30	50	–	mw/sr
Peak Emission Wavelength	λ_p	$I_F = 50\text{mA}$	–	940	–	nm
Spectrum Line Half-Width	$\Delta\lambda$	$I_F = 50\text{mA}$	–	50	–	nm

